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Power Matters[™]

Home ▶ JANTX2N6678T1 (#76763)

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Products

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Overview **Diagrams**

8.00 20.00 HFE DC Current Gain 3000.00 Turn Off Time (nS)

| Maximum Electrical Rating | Symbol | Min | Тур | Max | Unit |
|---------------------------------------|------------------|-----|-----|--------|------|
| Collector Current (dc) | I _C | | | 15.00 | Α |
| Collector-Emitter Voltage (Base Open) | V _{CEO} | | | 400.00 | V |
| Junction Temperature (°C) | T_J | | | 200.00 | °C |

This part can be found in the following product categories:

- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ NPN Transistor
- Discretes ► Transistors ► BJT(BiPolar Junction Transistor) ► NPN Transistor

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